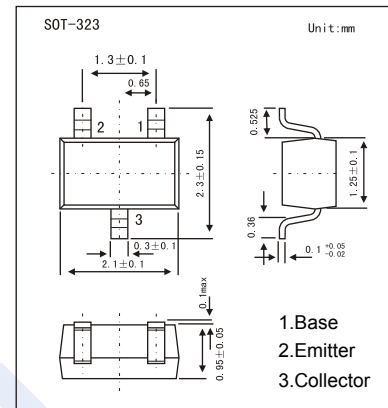


PNP Transistors

2SA1579

■ Features

- High breakdown voltage. ($BV_{CEO} = -120V$)
- Complements the 2SC4102.

■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CBO}	-120	V
Collector - Emitter Voltage	V_{CEO}	-120	
Emitter - Base Voltage	V_{EBO}	-5	
Collector Current - Continuous	I_C	-50	mA
Collector Power Dissipation	P_C	100	mW
Junction Temperature	T_J	150	$^\circ C$
Storage Temperature range	T_{stg}	-55 to 150	

■ Electrical Characteristics $T_a = 25^\circ C$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CBO}	$I_C = -50 \mu A, I_E = 0$	-120			V
Collector- emitter breakdown voltage	V_{CEO}	$I_C = -1 mA, I_B = 0$	-120			
Emitter - base breakdown voltage	V_{EBO}	$I_E = -50 \mu A, I_C = 0$	-5			
Collector-base cut-off current	I_{CBO}	$V_{CB} = -100 V, I_E = 0$			-0.5	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -4 V, I_C = 0$			-0.5	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -10 mA, I_B = -1 mA$			-0.5	V
Base - emitter saturation voltage	$V_{BE(sat)}$	$I_C = -10 mA, I_B = -1 mA$			-1.2	
DC current gain	h_{FE}	$V_{CE} = -6 V, I_C = -2 mA$	180		560	
Collector output capacitance	C_{ob}	$V_{CB} = -12 V, I_E = 0, f = 1 MHz$		3.2		pF
Transition frequency	f_T	$V_{CE} = -12 V, I_C = -2 mA, f = 30 MHz$		140		MHz

■ Classification of h_{FE}

Type	2SA1579-R	2SA1579-S
Range	180-390	270-560
Marking	RR	RS

PNP Transistors

2SA1579

■ Typical Characteristics

